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## INVITED PAPERS

- 121001 MOS Capacitance–Voltage Characteristics II. Sensitivity of Electronic Trapping at Dopant Impurity from Parameter Variations** (*11 pages*)  
Jie Binbin and Sah Chihtang
- 121002 MOS Capacitance–Voltage Characteristics III. Trapping Capacitance from 2-Charge-State Impurities** (*16 pages*)  
Jie Binbin and Sah Chihtang

## SEMICONDUCTOR PHYSICS

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Yang Shiyu, Cui Jingzhong, Tu Jianhui, and Liang Yaoting
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Li Hongli, Sun Yicai, Wang Wei, and Harry Hutchinson
- 122003 Peltier effect in doped silicon microchannel plates** (*4 pages*)  
Ci Pengliang, Shi Jing, Wang Fei, Xu Shaohui, Yang Zhenya, Yang Pingxiong, Wang Lianwei, Gao Chen, and Paul K. Chu

## SEMICONDUCTOR MATERIALS

- 123001 Influence of morphologies on the field emission performance of oriented ZnO nano-arrays** (*4 pages*)  
Wang Lingjie, Yang Zunxian, Lin Jinyang, and Guo Tailiang
- 123002 Selected area laser-crystallized polycrystalline silicon thin films by a pulsed Nd:YAG laser with 355 nm wavelength** (*5 pages*)  
Duan Chunyan, Liu Chao, Ai Bin, Lai Jianjun, Deng Youjun, and Shen Hui
- 123003 In situ nanoscale refinement by highly controllable etching of the (111) silicon crystal plane and its influence on the enhanced electrical property of a silicon nanowire** (*5 pages*)  
Gong Yibin, Dai Pengfei, Gao Anran, Li Tie, Zhou Ping, and Wang Yuelin

## SEMICONDUCTOR DEVICES

- 124001 Study and modeling of the transport mechanism in a Schottky diode on the basis of a GaAs semiinsulator** (*6 pages*)  
A. Resfa, Bourzig Y Smahi, and Brahim R Menezla
- 124002 Investigation and modeling of the avalanche effect in MOSFETs with non-uniform finger spacing** (*4 pages*)  
Liu Jun, Sun Lingling, and Marissa Condon
- 124003 A 4.69-W/mm output power density InAlN/GaN HEMT grown on sapphire substrate** (*4 pages*)  
Liu Bo, Feng Zhihong, Zhang Sen, Dun Shaobo, Yin Jiayun, Li Jia, Wang Jingjing, Zhang Xiaowei, Fang Yulong, and Cai Shujun
- 124004 Design and optimization of linearly graded-doping junction termination extension for 3.3-kV-class IGBTs** (*4 pages*)  
Jiang Huaping, Chen Wanjun, Liu Chuang, Rao Zugang, Dong Bin, and Zhang Bo

(Continued on inside back cover)

- 124005** **A novel high-voltage device structure with on N<sup>+</sup> ring in substrate and the breakdown voltage model** (4 pages)  
Li Qi, Zhu Jinluan, Wang Weidong, Yue Hongwei, and Jin Liangnian
- 124006** **Light controlled prebreakdown characteristics of a semi-insulating GaAs photoconductive switch** (6 pages)  
Ma Xiangrong, Shi Wei, Ji Weili, and Xue Hong
- 124007** **A novel 2-T structure memory device using a Si nanodot for embedded application** (5 pages)  
Yang Xiaonan, Wang Yong, Zhang Manhong, Huo Zongliang, Liu Jing, Zhang Bo, and Liu Ming
- 124008** **Collection efficiency and charge transfer optimization for a 4-T pixel with multi n-type implants** (4 pages)  
Li Weiping, Xu Jiangtao, Xu Chao, Li Binqiao, and Yao Suying

#### SEMICONDUCTOR INTEGRATED CIRCUITS

- 125001** **A dual-mode analog baseband with digital-assisted DC-offset calibration for WCDMA/GSM receivers** (6 pages)  
Xie Renzhong, Jiang Chen, Li Weinan, Huang Yumei, and Hong Zhiliang
- 125002** **A transformer-loaded receiver front end for 2.4 GHz WLAN in 0.13  $\mu$ m CMOS technology** (6 pages)  
Peng Miao, Lin Min, Shi Yin, and Fa Foster Dai
- 125003** **A new low-voltage and high-speed sense amplifier for flash memory** (5 pages)  
Guo Jiarong and Ran Feng
- 125004** **A novel power amplifier structure for RFID tag applications** (4 pages)  
Deng Jianbao, Zhang Shilin, Li De, Zhang Yanzheng, Mao Luhong, and Xie Sheng
- 125005** **Harmonic-suppressed quadrature-input frequency divider for OFDM systems** (5 pages)  
Fu Haipeng, Ren Junyan, Li Wei, and Li Ning
- 125006** **A 5 GHz 7.2 dB NF low power direct conversion receiver front-end with balun LNA** (7 pages)  
Hao Shilei, Mei Niansong, Huang Yumei, and Hong Zhiliang
- 125007** **Continuous time sigma delta ADC design and non-idealities analysis** (6 pages)  
Yuan Jun, Zhang Zhaofeng, Wu Jun, Wang Chao, Chen Zhenhai, Qian Wenrong, and Yang Yintang
- 125008** **A low power mixed signal DC offset calibration circuit for direct conversion receiver applications** (5 pages)  
Yang Lijun, Yuan Fang, Gong Zheng, Shi Yin, and Chen Zhiming
- 125009** **A 750 MHz semi-digital clock and data recovery circuit with 10<sup>-12</sup> BER** (5 pages)  
Wei Xueming, Wang Yiwen, Li Ping, and Luo Heping
- 125010** **12.5 Gbps 1:16 DEMUX IC with high speed synchronizing circuits** (5 pages)  
Zhou Lei, Wu Danyu, Chen Jianwu, Jin Zhi, and Liu Xinyu

#### SEMICONDUCTOR TECHNOLOGY

- 126001** **Improvement of the field emission properties of carbon nanotubes by CNT/Fe<sub>3</sub>O<sub>4</sub> composite electrophoretic deposition** (4 pages)  
Zheng Longwu, Hu Liqin, Yang Fan, and Guo Tailiang
- 126002** **Wafer back pressure control and optimization in the CMP process** (8 pages)  
Men Yanwu, Zhang Hui, Zhou Kai, and Ye Peiqing
- 129501** **Annual List of Contents to Volume 32** (16 pages)
- 129901** **Author Index to Volume 32** (18 pages)